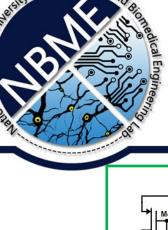


IoT Sensor Interface Circuit Chip Design

Author: 吳璨霖,蔡睿謙,顏子茗,Chih-Chieh (Morris) Fan

Advisor: Prof. Kea-Tiong (Samuel) Tang, Neuromorphic

and Biomedical Engineering Laboratory, NTHUEE.



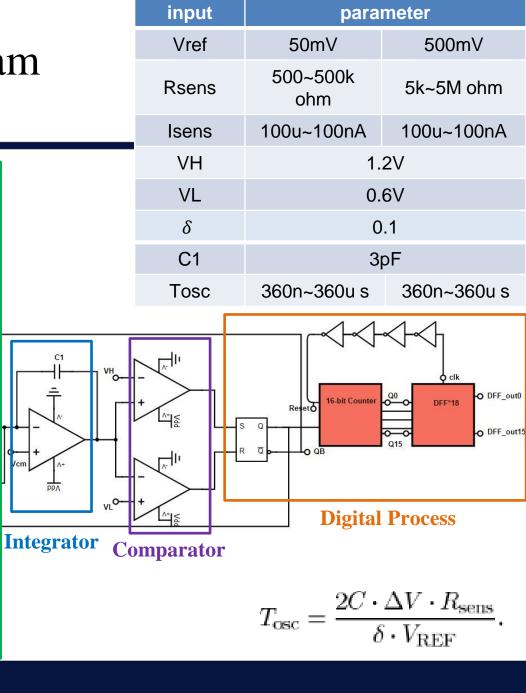
Isens

VtoI

System Diagram (.18 process)

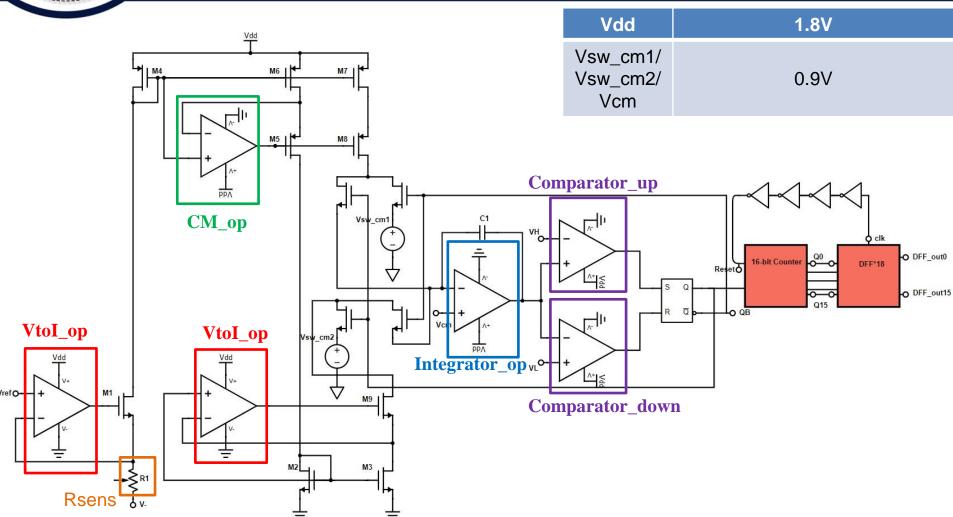
M9 |

Current Mirror

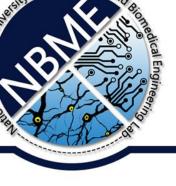




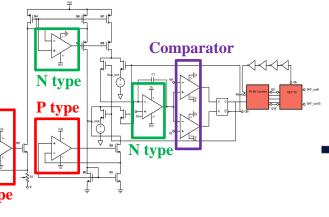
System Diagram (.18 process)

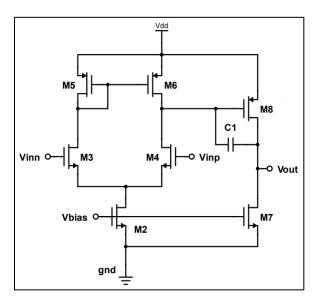


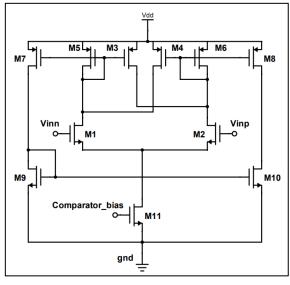
NTHU - NBME

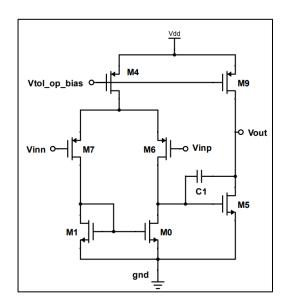


n/p type two stage OP





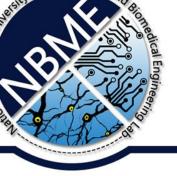




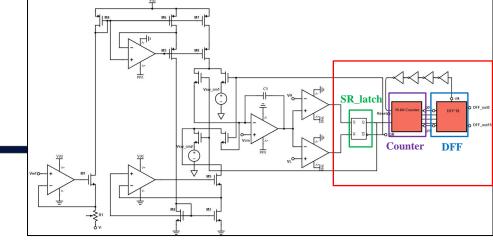
N type two stage op

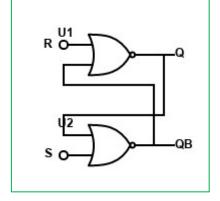
Comparator_op

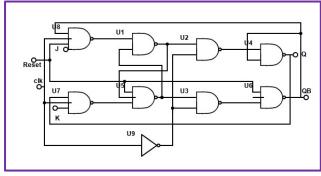
P type two stage op

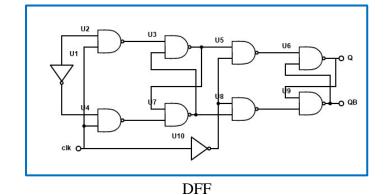


Digital Block



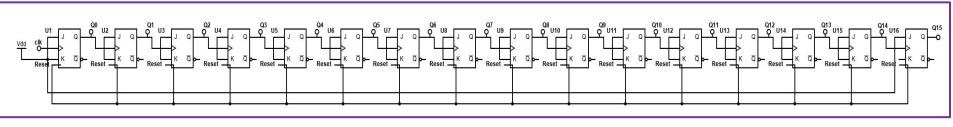




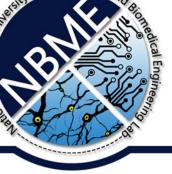


SR latch

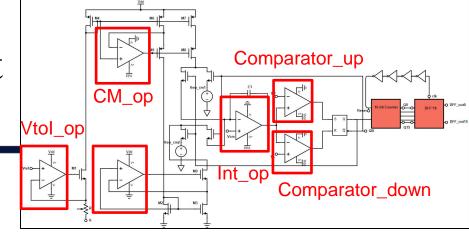
Counter JKFF Structure

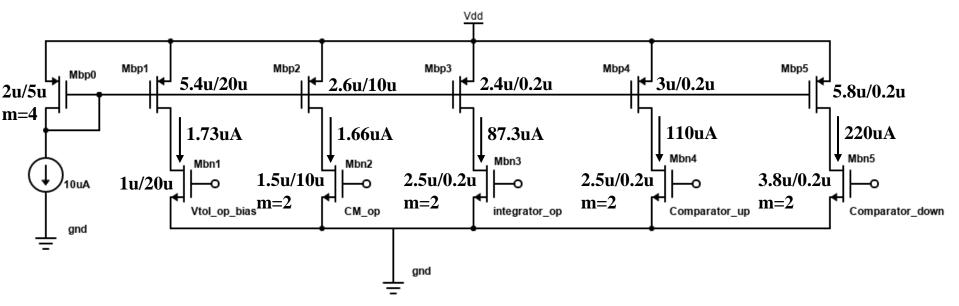


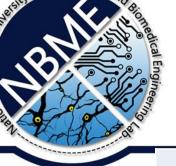
Counter



OP_Vbias Circuit mos sizing







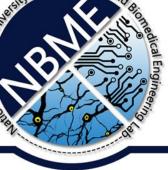
SPEC

Specification	Spec.	Pre-sim(TT)	Post-sim(TT)
Power Supply(V)	1.8V(Analog)	1.8V(Analog)	1.8V(Analog)
Dynamic Range	500Ω-5ΜΩ	500Ω-5ΜΩ	500Ω-5ΜΩ
Counter Output bit	16	16	16
Total Current (mA)	4.5	3.52~3.64	3.34~3.46
Total Power (VDD,mW)	8	6.336~6.552	6.012~6.228
Chip size(mm²)	<1.2 x 1.2		1.018 x 1.018
Integrator Range(ΔV)	0.6-1.2V	0.58 – 1.22V	0.58 – 1.22V



Specification	SPEC			
Dynamic range	500~5M			
CM Power	0.144mW			
Power supply	1.8V			
Output Bit	17			
Variable parameter				
Rsens	500~5M			
ΔV	0.6V			
С	3pF			
δ	0.1			

	Vref = 50mV	Vref = 500mV
	500~500kΩ	5k~5MΩ
δ	0.1	0.1
Isens	100uA~0.1uA	100uA~0.1uA
С	3pF	3pF
ΔV	0.6V	0.6V
fmax	2.78M	2.78M
fmin	2.78k	2.78k

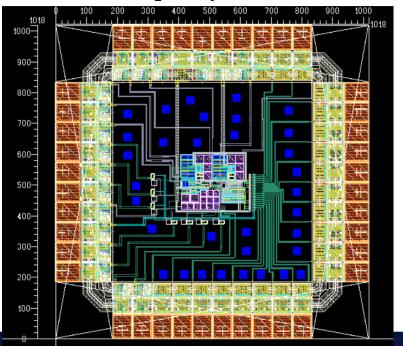


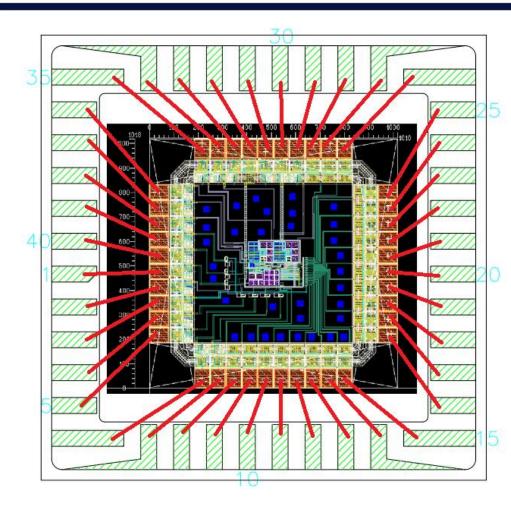
Layout and Wiring

•Chip Size: 1018*1018 um^2

•Power Dissipation : 6.55mW

•Max Frequency: 2.78MHz







Layout and Placing

